

Weida Hu

List of Publications by Year in descending order

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317
papers

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8208

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323
times ranked

18158
citing authors

#	ARTICLE	IF	CITATIONS
1	Composition and phase engineering of metal chalcogenides and phosphorous chalcogenides. <i>Nature Materials</i> , 2023, 22, 450-458.	13.3	62
2	Emerging Single-Photon Detectors Based on Low-Dimensional Materials. <i>Small</i> , 2022, 18, e2103963.	5.2	23
3	All-in-one two-dimensional retinomorphic hardware device for motion detection and recognition. <i>Nature Nanotechnology</i> , 2022, 17, 27-32.	15.6	187
4	Fast Uncooled Mid-Wavelength Infrared Photodetectors with Heterostructures of van der Waals on Epitaxial HgCdTe. <i>Advanced Materials</i> , 2022, 34, e2107772.	11.1	58
5	Van der Waals two-color infrared photodetector. <i>Light: Science and Applications</i> , 2022, 11, 6.	7.7	97
6	Macroscopic assembled graphene nanofilms based room temperature ultrafast mid-infrared photodetectors. <i>Information Materials</i> , 2022, 4, .	8.5	24
7	Next-generation machine vision systems incorporating two-dimensional materials: Progress and perspectives. <i>Information Materials</i> , 2022, 4, .	8.5	58
8	HgCdTe/black phosphorus van der Waals heterojunction for high-performance polarization-sensitive midwave infrared photodetector. <i>Science Advances</i> , 2022, 8, eabn1811.	4.7	50
9	Room-Temperature Blackbody-Sensitive and Fast Infrared Photodetectors Based on 2D Tellurium/Graphene Van der Waals Heterojunction. <i>ACS Photonics</i> , 2022, 9, 1775-1782.	3.2	27
10	Near-infrared heterojunction field modulated phototransistors with distinct photodetection/photostorage switching features for artificial visuals. <i>Journal of Materials Chemistry C</i> , 2022, 10, 9198-9207.	2.7	3
11	Graphene-assisted metal transfer printing for wafer-scale integration of metal electrodes and two-dimensional materials. <i>Nature Electronics</i> , 2022, 5, 275-280.	13.1	61
12	High-operating temperature far-infrared Si:Ga blocked-impurity-band detectors. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3
13	“Clean” doping to advance 2D material phototransistors. <i>Light: Science and Applications</i> , 2022, 11, .	7.7	2
14	Pristine PN junction toward atomic layer devices. <i>Light: Science and Applications</i> , 2022, 11, .	7.7	21
15	Ultra-sensitive polarization-resolved black phosphorus homojunction photodetector defined by ferroelectric domains. <i>Nature Communications</i> , 2022, 13, .	5.8	77
16	High responsivity and flexible deep-UV phototransistor based on Ta-doped $\text{In}^{2-}\text{Ga}_2\text{O}_3$. <i>Npj Flexible Electronics</i> , 2022, 6, .	5.1	28
17	Progress and challenges in blocked impurity band infrared detectors for space-based astronomy. <i>Science China: Physics, Mechanics and Astronomy</i> , 2022, 65, .	2.0	5
18	Gate Stack Engineering in MoS_2 Field-Effect Transistor for Reduced Channel Doping and Hysteresis Effect. <i>Advanced Electronic Materials</i> , 2021, 7, 2000395.	2.6	19

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19	Recent progress and challenges on two-dimensional material photodetectors from the perspective of advanced characterization technologies. Nano Research, 2021, 14, 1840-1862.	5.8	36
20	Extrinsic Photoconduction Induced Short-Wavelength Infrared Photodetectors Based on Ge-Based Chalcogenides. Small, 2021, 17, e2006765.	5.2	25
21	Direct Polarimetric Image Sensor and Wide Spectral Response Based on Quasi-1D Sb ₂ S ₃ Nanowire. Advanced Functional Materials, 2021, 31, 2006601.	7.8	52
22	Trends in Performance Limits of the HOT Infrared Photodetectors. Applied Sciences (Switzerland), 2021, 11, 501.	1.3	48
23	Infrared Gesture Recognition System Based on Near-Sensor Computing. IEEE Electron Device Letters, 2021, 42, 1053-1056.	2.2	8
24	Corrections to "Optimized Si-Based Blocked Impurity Band Detector Under Alternative Operational Mode" [Sep 19 3891-3895]. IEEE Transactions on Electron Devices, 2021, 68, 447-447.	1.6	0
25	Reversible engineering of topological insulator surface state conductivity through optical excitation. Nanotechnology, 2021, 32, 17LT01.	1.3	3
26	Fabrication of 1D Te/2D ReS ₂ Mixed-Dimensional van der Waals <i>p-n</i> Heterojunction for High-Performance Phototransistor. ACS Nano, 2021, 15, 3241-3250.	7.3	91
27	Stoichiometric effect on electrical and near-infrared photodetection properties of full-composition-range GaAs _{1-x} Sb _x nanowires. Nano Research, 2021, 14, 3961-3968.	5.8	12
28	Narrowing Bandgap of HfS ₂ by Te Substitution for Short-Wavelength Infrared Photodetection. Advanced Optical Materials, 2021, 9, 2002248.	3.6	17
29	Gate-Tunable Photodiodes Based on Mixed-Dimensional Te/MoTe ₂ Van der Waals Heterojunctions. Advanced Electronic Materials, 2021, 7, 2001066.	2.6	29
30	Simultaneous control of intensity, phase, and polarization in real time under a weak oscillation theory. Optics Letters, 2021, 46, 1361.	1.7	5
31	Interface engineering of ferroelectric-gated MoS ₂ phototransistor. Science China Information Sciences, 2021, 64, 1.	2.7	10
32	Spatial description theory of narrow-band single-carrier avalanche photodetectors. Optics Express, 2021, 29, 16432.	1.7	12
33	Broadband Photodetectors: Broadband Bi ₂ O ₃ Se Photodetectors from Infrared to Terahertz (Adv. Funct. Mater. 14/2021). Advanced Functional Materials, 2021, 31, 2170093.	7.8	3
34	Blackbody-sensitive room-temperature infrared photodetectors based on low-dimensional tellurium grown by chemical vapor deposition. Science Advances, 2021, 7, .	4.7	121
35	Recent Progress on Electrical and Optical Manipulations of Perovskite Photodetectors. Advanced Science, 2021, 8, e2100569.	5.6	118
36	Unipolar barrier photodetectors based on van der Waals heterostructures. Nature Electronics, 2021, 4, 357-363.	13.1	292

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37	Ternary 2D Layered Material FePSe ₃ and Near-Infrared Photodetector. <i>Advanced Electronic Materials</i> , 2021, 7, 2100207.	2.6	19
38	Logic gates based on neuristors made from two-dimensional materials. <i>Nature Electronics</i> , 2021, 4, 399-404.	13.1	95
39	Down-Scalable and Ultra-fast Memristors with Ultra-high Density Three-Dimensional Arrays of Perovskite Quantum Wires. <i>Nano Letters</i> , 2021, 21, 5036-5044.	4.5	53
40	Ferroelectric-tuned van der Waals heterojunction with band alignment evolution. <i>Nature Communications</i> , 2021, 12, 4030.	5.8	79
41	Optoelectronic Synapses Based on Photo-Induced Doping in MoS ₂ /hBN Field-Effect Transistors. <i>Advanced Optical Materials</i> , 2021, 9, 2100937.	3.6	25
42	Skin effect photon-trapping enhancement in infrared photodiodes. <i>Optics Express</i> , 2021, 29, 22823.	1.7	6
43	Slowing Hot-Electron Relaxation in Mix-Phase Nanowires for Hot-Carrier Photovoltaics. <i>Nano Letters</i> , 2021, 21, 7761-7768.	4.5	15
44	Stable and sensitive tin-lead perovskite photodetectors enabled by azobenzene derivative for near-infrared acousto-optic conversion communications. <i>Nano Energy</i> , 2021, 86, 106113.	8.2	68
45	Probability Theory of Single-Carrier Avalanche in HgCdTe APDs as a Stochastic Process. , 2021, , .		0
46	2D materials-based homogeneous transistor-memory architecture for neuromorphic hardware. <i>Science</i> , 2021, 373, 1353-1358.	6.0	177
47	Controllable Doping in 2D Layered Materials. <i>Advanced Materials</i> , 2021, 33, e2104942.	11.1	59
48	Extended Infrared responses in Er/O-Hyperdoped Si at Room Temperature. <i>Optics Letters</i> , 2021, 46, 5165-5168.	1.7	6
49	Broadband Bi ₂ O ₂ Se Photodetectors from Infrared to Terahertz. <i>Advanced Functional Materials</i> , 2021, 31, 2009554.	7.8	65
50	Polarizer-free polarimetric image sensor through anisotropic two-dimensional GeSe. <i>Science China Materials</i> , 2021, 64, 1230-1237.	3.5	21
51	Direct observation and manipulation of hot electrons at room temperature. <i>National Science Review</i> , 2021, 8, nwaa295.	4.6	16
52	Recent Progress on Two-Dimensional Materials. <i>Wuli Huaxue Xuebao/ Acta Physico - Chimica Sinica</i> , 2021, .	2.2	269
53	Substitutionally Doped MoSe ₂ for High-Performance Electronics and Optoelectronics. <i>Small</i> , 2021, 17, e2102855.	5.2	24
54	Coexistence of Photoelectric Conversion and Storage in van der Waals Heterojunctions. <i>Physical Review Letters</i> , 2021, 127, 217401.	2.9	13

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55	Silicon: quantum dot photovoltage triodes. <i>Nature Communications</i> , 2021, 12, 6696.	5.8	22
56	Temperature-sensitive mechanism for silicon blocked-impurity-band photodetectors. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	6
57	Graphene Hybrid Structures for Integrated and Flexible Optoelectronics. <i>Advanced Materials</i> , 2020, 32, e1902039.	11.1	127
58	Light-Driven WSe ₂ /ZnO Junction Field-Effect Transistors for High-Performance Photodetection. <i>Advanced Science</i> , 2020, 7, 1901637.	5.6	66
59	A Noble Metal Dichalcogenide for High-Performance Field-Effect Transistors and Broadband Photodetectors. <i>Advanced Functional Materials</i> , 2020, 30, 1907945.	7.8	72
60	Ultrasensitive negative capacitance phototransistors. <i>Nature Communications</i> , 2020, 11, 101.	5.8	124
61	Enhanced Performance of HgCdTe Midwavelength Infrared Electron Avalanche Photodetectors With Guard Ring Designs. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 542-546.	1.6	19
62	Edge-Epitaxial Growth of InSe Nanowires toward High-Performance Photodetectors. <i>Small</i> , 2020, 16, e1905902.	5.2	22
63	Flexible Quasi-2D Perovskite/IGZO Phototransistors for Ultrasensitive and Broadband Photodetection. <i>Advanced Materials</i> , 2020, 32, e1907527.	11.1	88
64	Toward Scalable Fabrication of Atomic Wires in Silicon by Nanopatterning Self-Assembled Molecular Monolayers. <i>ACS Applied Electronic Materials</i> , 2020, 2, 275-281.	2.0	2
65	Ambipolar and Robust WSe ₂ Field-Effect Transistors Utilizing Self-Assembled Edge Oxides. <i>Advanced Materials Interfaces</i> , 2020, 7, 1901628.	1.9	11
66	A Dual-Gate MoS ₂ Photodetector Based on Interface Coupling Effect. <i>Small</i> , 2020, 16, e1904369.	5.2	65
67	Air-Stable Low-Symmetry Narrow-Bandgap 2D Sulfide Niobium for Polarization Photodetection. <i>Advanced Materials</i> , 2020, 32, e2005037.	11.1	68
68	Surface-States-Modulated High-Performance InAs Nanowire Phototransistor. <i>Journal of Physical Chemistry Letters</i> , 2020, 11, 6413-6419.	2.1	21
69	Highly Sensitive InSb Nanosheets Infrared Photodetector Passivated by Ferroelectric Polymer. <i>Advanced Functional Materials</i> , 2020, 30, 2006156.	7.8	41
70	Light-modulated vertical heterojunction phototransistors with distinct logical photocurrents. <i>Light: Science and Applications</i> , 2020, 9, 167.	7.7	40
71	Bi ₂ O ₂ Se/Au-Based Schottky Phototransistor With Fast Response and Ultrahigh Responsivity. <i>IEEE Electron Device Letters</i> , 2020, 41, 1464-1467.	2.2	5
72	A versatile photodetector assisted by photovoltaic and bolometric effects. <i>Light: Science and Applications</i> , 2020, 9, 160.	7.7	56

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73	Stable mid-infrared polarization imaging based on quasi-2D tellurium at room temperature. <i>Nature Communications</i> , 2020, 11, 2308.	5.8	259
74	Ultrabroadband Photodetectors up to 10.6 μm Based on 2D Fe_3O_4 Nanosheets. <i>Advanced Materials</i> , 2020, 32, e2002237.	11.1	57
75	Gate-Tunable Semiconductor Heterojunctions from 2D/3D van der Waals Interfaces. <i>Nano Letters</i> , 2020, 20, 2907-2915.	4.5	69
76	Ultrafast and broadband photodetectors based on a perovskite/organic bulk heterojunction for large-dynamic-range imaging. <i>Light: Science and Applications</i> , 2020, 9, 31.	7.7	372
77	Epitaxial growth of metal-semiconductor van der Waals heterostructures $\text{NbS}_2/\text{MoS}_2$ with enhanced performance of transistors and photodetectors. <i>Science China Materials</i> , 2020, 63, 1548-1559.	3.5	40
78	High-Performance Broadband Tungsten Disulfide Photodetector Decorated with Indium Arsenide Nanoislands. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2000297.	0.8	2
79	MoTe_2 π -Homojunctions Defined by Ferroelectric Polarization. <i>Advanced Materials</i> , 2020, 32, e1907937.	11.1	115
80	Two-dimensional series connected photovoltaic cells defined by ferroelectric domains. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	10
81	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. <i>Nature Electronics</i> , 2020, 3, 43-50.	13.1	167
82	Multicolor Broadband and Fast Photodetector Based on $\text{InGaAs}/\text{Insulator}/\text{Graphene}$ Hybrid Heterostructure. <i>Advanced Electronic Materials</i> , 2020, 6, 1901007.	2.6	44
83	Enhanced Performance of HgCdTe Long-Wavelength Infrared Photodetectors With nBn Design. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 2001-2007.	1.6	18
84	Multifunctional MoS_2 Transistors with Electrolyte Gel Gating. <i>Small</i> , 2020, 16, e2000420.	5.2	23
85	Non-layered ZnSb nanoplates for room temperature infrared polarized photodetectors. <i>Journal of Materials Chemistry C</i> , 2020, 8, 6388-6395.	2.7	24
86	Ferroelectric Enhanced Performance of a GeSn/Ge Dual-Nanowire Photodetector. <i>Nano Letters</i> , 2020, 20, 3872-3879.	4.5	33
87	Optically and electrically modulated printed carbon nanotube synaptic transistors with a single input terminal and multi-functional output characteristics. <i>Journal of Materials Chemistry C</i> , 2020, 8, 6914-6922.	2.7	11
88	Design of a bandgap-engineered barrier-blocking HOT HgCdTe long-wavelength infrared avalanche photodiode. <i>Optics Express</i> , 2020, 28, 33556.	1.7	22
89	Enhanced Photoresponsivity of a GaAs Nanowire Metal-Semiconductor-Metal Photodetector by Adjusting the Fermi Level. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 33188-33193.	4.0	151
90	Ultrabroad-Spectrum Photodetectors: Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 μm (<i>Adv. Sci.</i> 15/2019). <i>Advanced Science</i> , 2019, 6, 1970089.	5.6	2

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91	Light-Induced Positive and Negative Photoconductances of InAs Nanowires toward Rewritable Nonvolatile Memory. <i>ACS Applied Electronic Materials</i> , 2019, 1, 1825-1831.	2.0	14
92	Ultrahigh Hole Mobility of Sn-Catalyzed GaSb Nanowires for High Speed Infrared Photodetectors. <i>Nano Letters</i> , 2019, 19, 5920-5929.	4.5	61
93	Modulated Metal-Insulator Transition Behaviors in Vanadium Dioxide Nanowires with an Artificial Oxidized Domain. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1900383.	1.2	8
94	High efficiency and fast van der Waals hetero-photodiodes with a unilateral depletion region. <i>Nature Communications</i> , 2019, 10, 4663.	5.8	213
95	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional Bi ₂ O ₂ Se Nanosheets. <i>Advanced Functional Materials</i> , 2019, 29, 1905806.	7.8	106
96	MoS ₂ /HfO ₂ /Silicon-On-Insulator Dual-Photogating Transistor with Ambipolar Photoresponsivity for High-Resolution Light Wavelength Detection. <i>Advanced Functional Materials</i> , 2019, 29, 1906242.	7.8	22
97	Sensing Infrared Photons at Room Temperature: From Bulk Materials to Atomic Layers. <i>Small</i> , 2019, 15, e1904396.	5.2	83
98	A study on ionic gated MoS ₂ phototransistors. <i>Science China Information Sciences</i> , 2019, 62, 1.	2.7	8
99	Anomalous Broadband Spectrum Photodetection in 2D Rhenium Disulfide Transistor. <i>Advanced Optical Materials</i> , 2019, 7, 1901115.	3.6	37
100	A gate-free MoS ₂ phototransistor assisted by ferroelectrics. <i>Journal of Semiconductors</i> , 2019, 40, 092002.	2.0	10
101	Nb ₂ SiTe ₄ : A Stable Narrow-Gap Two-Dimensional Material with Ambipolar Transport and Mid-Infrared Response. <i>ACS Nano</i> , 2019, 13, 10705-10710.	7.3	48
102	Global Photocurrent Generation in Phototransistors Based on Single-Walled Carbon Nanotubes toward Highly Sensitive Infrared Detection. <i>Advanced Optical Materials</i> , 2019, 7, 1900597.	3.6	15
103	Time-Tailoring van der Waals Heterostructures for Human Memory System Programming. <i>Advanced Science</i> , 2019, 6, 1901072.	5.6	52
104	Optimized Si-Based Blocked Impurity Band Detector Under Alternative Operational Mode. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 3891-3895.	1.6	7
105	Magnetism and Optical Anisotropy in van der Waals Antiferromagnetic Insulator CrOCl. <i>ACS Nano</i> , 2019, 13, 11353-11362.	7.3	97
106	Multimode Signal Processor Unit Based on the Ambipolar WSe ₂ -Cr Schottky Junction. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 38895-38901.	4.0	3
107	Observation of ballistic avalanche phenomena in nanoscale vertical InSe/BP heterostructures. <i>Nature Nanotechnology</i> , 2019, 14, 217-222.	15.6	153
108	AsP/InSe Van der Waals Tunneling Heterojunctions with Ultrahigh Reverse Rectification Ratio and High Photosensitivity. <i>Advanced Functional Materials</i> , 2019, 29, 1900314.	7.8	121

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109	Symmetric Ultrafast Writing and Erasing Speeds in Quasi-Nonvolatile Memory via van der Waals Heterostructures. <i>Advanced Materials</i> , 2019, 31, e1808035.	11.1	50
110	Controllable Growth of Lead-Free All-Inorganic Perovskite Nanowire Array with Fast and Stable Near-Infrared Photodetection. <i>Journal of Physical Chemistry C</i> , 2019, 123, 17566-17573.	1.5	78
111	Amorphous Gallium Oxide-Based Gate-Tunable High-Performance Thin Film Phototransistor for Solar-Blind Imaging. <i>Advanced Electronic Materials</i> , 2019, 5, 1900389.	2.6	95
112	Highly Polarized Photoelectrical Response in vdW ZrS ₃ Nanoribbons. <i>Advanced Electronic Materials</i> , 2019, 5, 1900419.	2.6	45
113	Ultrasensitive Hybrid MoS ₂ -ZnCdSe Quantum Dot Photodetectors with High Gain. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 23667-23672.	4.0	62
114	Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 Åm. <i>Advanced Science</i> , 2019, 6, 1901050.	5.6	52
115	Etching Techniques in 2D Materials. <i>Advanced Materials Technologies</i> , 2019, 4, 1900064.	3.0	50
116	Vapor growth of CdS nanowires/WS ₂ nanosheet heterostructures with sensitive photodetections. <i>Nanotechnology</i> , 2019, 30, 345603.	1.3	18
117	Enhancement-mode CdS nanobelts field effect transistors and phototransistors with HfO ₂ passivation. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	6
118	Memory Devices: Symmetric Ultrafast Writing and Erasing Speeds in Quasi-Nonvolatile Memory via van der Waals Heterostructures (Adv. Mater. 11/2019). <i>Advanced Materials</i> , 2019, 31, 1970081.	11.1	0
119	Characterization of atomic defects on the photoluminescence in two-dimensional materials using transmission electron microscope. <i>Informa-Materials</i> , 2019, 1, 85-97.	8.5	46
120	Ultrahigh-Detectivity Photodetectors with Van der Waals Epitaxial CdTe Single-Crystalline Films. <i>Small</i> , 2019, 15, e1900236.	5.2	27
121	Artificial control of in-plane anisotropic photoelectricity in monolayer MoS ₂ . <i>Applied Materials Today</i> , 2019, 15, 203-211.	2.3	45
122	Optoelectronic Properties of Printed Photogating Carbon Nanotube Thin Film Transistors and Their Application for Light-Stimulated Neuromorphic Devices. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 12161-12169.	4.0	80
123	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. <i>ACS Nano</i> , 2019, 13, 3492-3499.	7.3	45
124	WSe ₂ Photovoltaic Device Based on Intramolecular p-n Junction. <i>Small</i> , 2019, 15, e1805545.	5.2	78
125	PtTe ₂ -Based Type-II Dirac Semimetal and Its van der Waals Heterostructure for Sensitive Room Temperature Terahertz Photodetection. <i>Small</i> , 2019, 15, e1903362.	5.2	98
126	Atomic Layered 2d/3d Heterostructure for Sensitive Photodetection. , 2019, , .		2

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127	TMD-Based Phototransistors: Anomalous Broadband Spectrum Photodetection in 2D Rhenium Disulfide Transistor (Advanced Optical Materials 23/2019). Advanced Optical Materials, 2019, 7, 1970088.	3.6	0
128	Progress, Challenges, and Opportunities for 2D Material Based Photodetectors. Advanced Functional Materials, 2019, 29, 1803807.	7.8	884
129	High performance charge-transfer induced homojunction photodetector based on ultrathin ZnO nanosheet. Applied Physics Letters, 2019, 114, .	1.5	21
130	Controlled Doping of Wafer-Scale PtSe ₂ Films for Device Application. Advanced Functional Materials, 2019, 29, 1805614.	7.8	87
131	Palladium Diselenide Long-Wavelength Infrared Photodetector with High Sensitivity and Stability. ACS Nano, 2019, 13, 2511-2519.	7.3	198
132	Optoelectronics: High-Performance Photovoltaic Detector Based on MoTe ₂ /MoS ₂ Van der Waals Heterostructure (Small 9/2018). Small, 2018, 14, 1870038.	5.2	7
133	Emission Kinetics from PbSe Quantum Dots in Glass Matrix at High Excitation Levels. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800012.	1.2	1
134	WSe ₂ /GeSe heterojunction photodiode with giant gate tunability. Nano Energy, 2018, 49, 103-108.	8.2	73
135	Intrinsic Single Crystal of a Lead-Free Organic-Inorganic Hybrid Perovskite for High-Performance Photodetector. Advanced Functional Materials, 2018, 28, 1705467.	7.8	146
136	Graphene Dirac point tuned by ferroelectric polarization field. Nanotechnology, 2018, 29, 134002.	1.3	15
137	High-Performance Photovoltaic Detector Based on MoTe ₂ /MoS ₂ Van der Waals Heterostructure. Small, 2018, 14, 1703293.	5.2	205
138	Novel Type-II InAs/AlSb Core-Shell Nanowires and Their Enhanced Negative Photocurrent for Efficient Photodetection. Advanced Functional Materials, 2018, 28, 1705382.	7.8	36
139	The ambipolar evolution of a high-performance WSe ₂ transistor assisted by a ferroelectric polymer. Nanotechnology, 2018, 29, 105202.	1.3	20
140	Ferroelectric Localized Field-Enhanced ZnO Nanosheet Ultraviolet Photodetector with High Sensitivity and Low Dark Current. Small, 2018, 14, e1800492.	5.2	85
141	Significant Enhancement of Single-Walled Carbon Nanotube Based Infrared Photodetector Using PbS Quantum Dots. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-8.	1.9	19
142	Influencing Sources for Dark Current Transport and Avalanche Mechanisms in Planar and Mesa HgCdTe p-i-n Electron-Avalanche Photodiodes. IEEE Transactions on Electron Devices, 2018, 65, 572-576.	1.6	44
143	Numerical simulation of HgCdTe nBn long-wavelength infrared detector. , 2018, , .		0
144	Surface Plasmon Polaritons Scattering by Strong Magnetic field in Two-dimensional Material. , 2018, , .		0

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145	Perpendicular Optical Reversal of the Linear Dichroism and Polarized Photodetection in 2D GeAs. ACS Nano, 2018, 12, 12416-12423.	7.3	157
146	Analysis of the relationship between the contact barrier and rectification ratio in a two-dimensional Pn heterojunction. Semiconductor Science and Technology, 2018, 33, 114012.	1.0	8
147	Ambipolar Graphene Quantum Dot Phototransistors with CMOS Compatibility. Advanced Optical Materials, 2018, 6, 1800985.	3.6	50
148	High-Performance Wafer-Scale MoS ₂ Transistors toward Practical Application. Small, 2018, 14, e1803465.	5.2	88
149	A Colloidal Quantum Dot Infrared Photodiode with High Photoconductive Gain. Small, 2018, 14, e1803158.	5.2	39
150	Complementary Logic with Voltage Zero-Loss and Nano-Watt Power via Configurable MoS ₂ /WSe ₂ Gate. Advanced Functional Materials, 2018, 28, 1805171.	7.8	32
151	Ultrahigh photoresponsivity MoS ₂ photodetector with tunable photocurrent generation mechanism. Nanotechnology, 2018, 29, 485204.	1.3	35
152	Diamond-Based All-Carbon Photodetectors for Solar-Blind Imaging. Advanced Optical Materials, 2018, 6, 1800068.	3.6	117
153	Exploring a Polar Two-dimensional Multi-layered Hybrid Perovskite of (C ₅ H ₁₁ NH ₃) ₂ (CH ₃ NH ₃) ₂ Pb ₂ I ₇ for Ultrafast-Responding Photodetection. Laser and Photonics Reviews, 2018, 12, 1800060.	1.6	16
154	Solution-Processed 3D RGO-MoS ₂ /Pyramid Si Heterojunction for Ultrahigh Detectivity and Ultra-Broadband Photodetection. Advanced Materials, 2018, 30, e1801729.	11.1	175
155	Negative Photoconductance in van der Waals Heterostructure-Based Floating Gate Phototransistor. ACS Nano, 2018, 12, 9513-9520.	7.3	124
156	Independent Band Modulation in 2D van der Waals Heterostructures via a Novel Device Architecture. Advanced Science, 2018, 5, 1800237.	5.6	36
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158	High-Performance Near-Infrared Photodetectors Based on p-Type SnX (X = S, Se) Nanowires Grown via Chemical Vapor Deposition. ACS Nano, 2018, 12, 7239-7245.	7.3	101
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